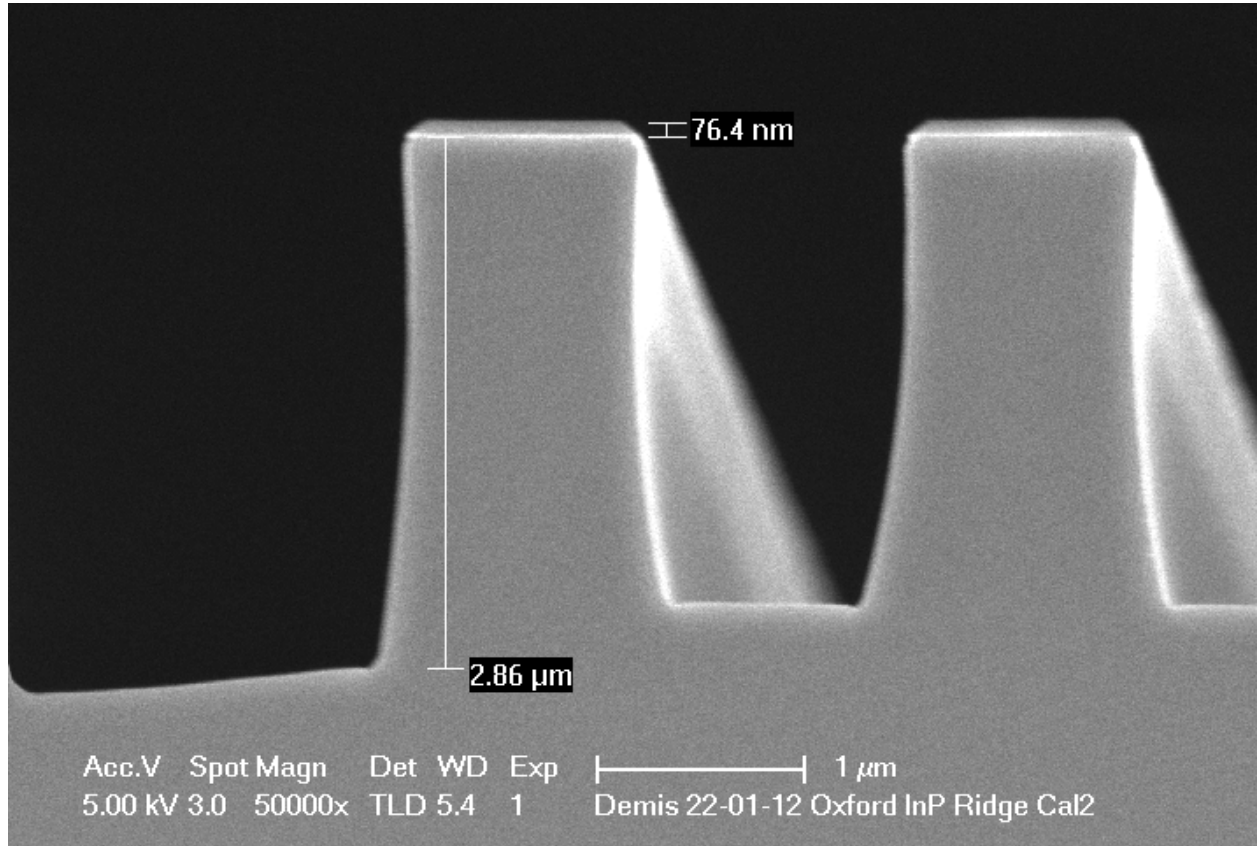


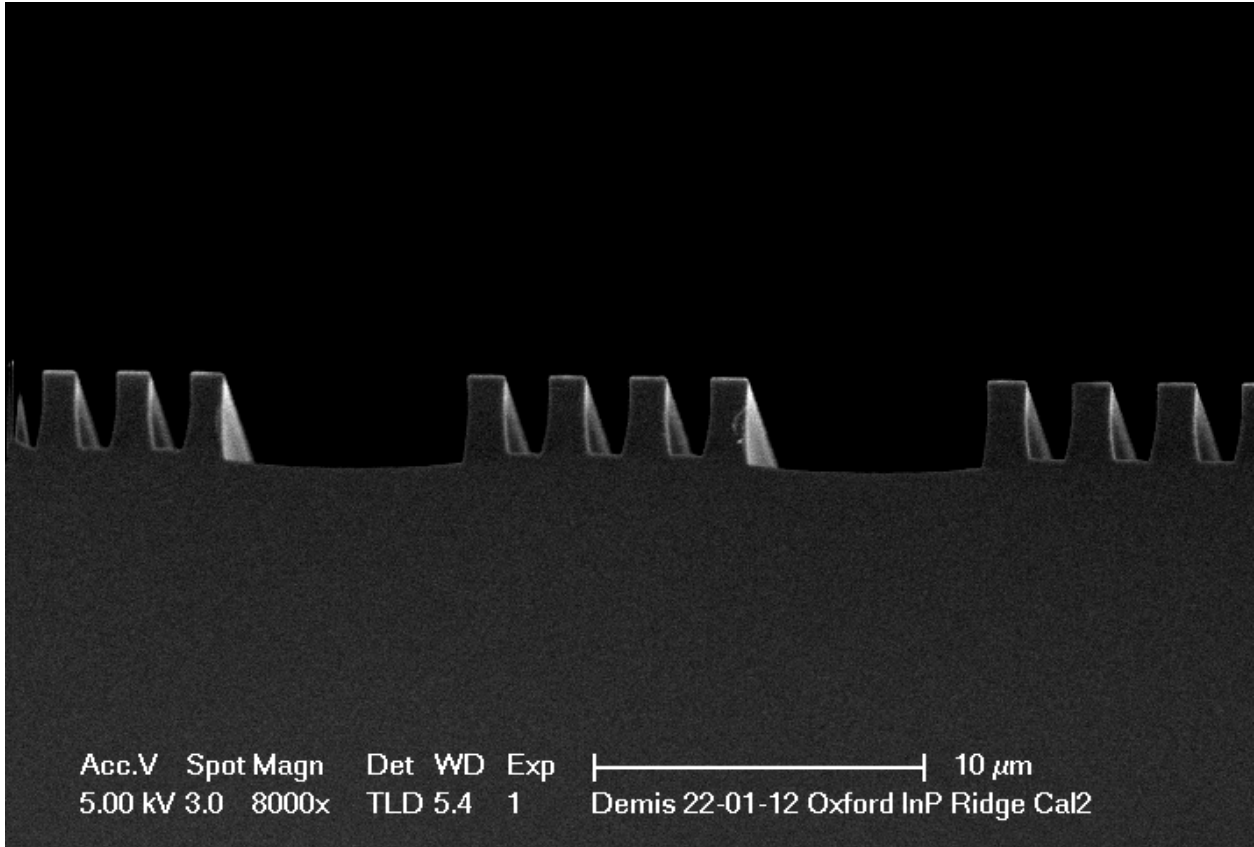
2022-01-11 DJ Cal – InP Ridge Process

Ning's "InP Wafer" patterned samples

Oxford ICP "InP Ridge Etch":

3mT, 800W/65W, Cl<sub>2</sub>=18, H<sub>2</sub>=15, CH<sub>4</sub>=10sccm, time=5min05sec (305sec)





Acc.V	Spot	Magn	Det	WD	Exp	—————	10 μm
5.00 kV	3.0	8000x	TLD	5.4	1	Demis 22-01-12	Oxford InP Ridge Cal2

